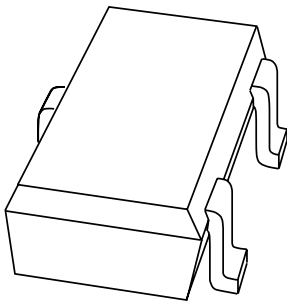


DATA SHEET



BFS540

NPN 9 GHz wideband transistor

Product specification
Supersedes data of 1997 Dec 05

2000 May 30

NPN 9 GHz wideband transistor

BFS540

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability
- SOT323 package.

APPLICATIONS

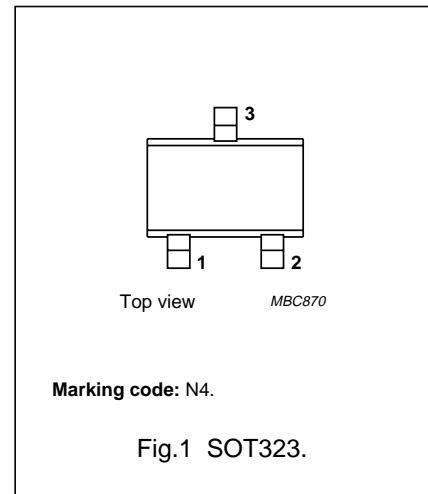
RF wideband amplifier applications such as satellite TV systems and RF portable communication equipment with signal frequencies up to 2 GHz.

DESCRIPTION

NPN transistor in a SOT323 plastic package.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	DC collector current		–	–	120	mA
P_{tot}	total power dissipation	$T_s \leq 80\text{ }^\circ\text{C}$; note 1	–	–	500	mW
h_{FE}	DC current gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	100	120	250	
f_T	transition frequency	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	14	–	dB
F	noise figure	$I_C = 10\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	1.3	1.7	dB

Note

1. T_s is the temperature at the soldering point of the collector tab.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	DC collector current		–	120	mA
P_{tot}	total power dissipation	$T_s \leq 80\text{ }^\circ\text{C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	150	$^\circ\text{C}$
T_j	junction temperature		–	175	$^\circ\text{C}$

Note

1. T_s is the temperature at the soldering point of the collector tab.

NPN 9 GHz wideband transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$T_s \leq 80\text{ °C}$; note 1	190	K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CE} = 8\text{ V}$	–	–	50	nA
h_{FE}	DC current gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$	100	120	250	
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$	–	2	–	pF
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 8\text{ V}$; $f = 1\text{ MHz}$	–	0.9	–	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 8\text{ V}$; $f = 1\text{ MHz}$	–	0.6	–	pF
f_T	transition frequency	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain (note 1)	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	14	–	dB
		$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	8	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	12	13	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 10\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.3	1.8	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.9	2.4	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 10\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	2.1	–	dB
P_{L1}	output power at 1 dB gain compression	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $R_L = 50\text{ }\Omega$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	21	–	dBm
ITO	third order intercept point	note 2	–	34	–	dBm

Notes

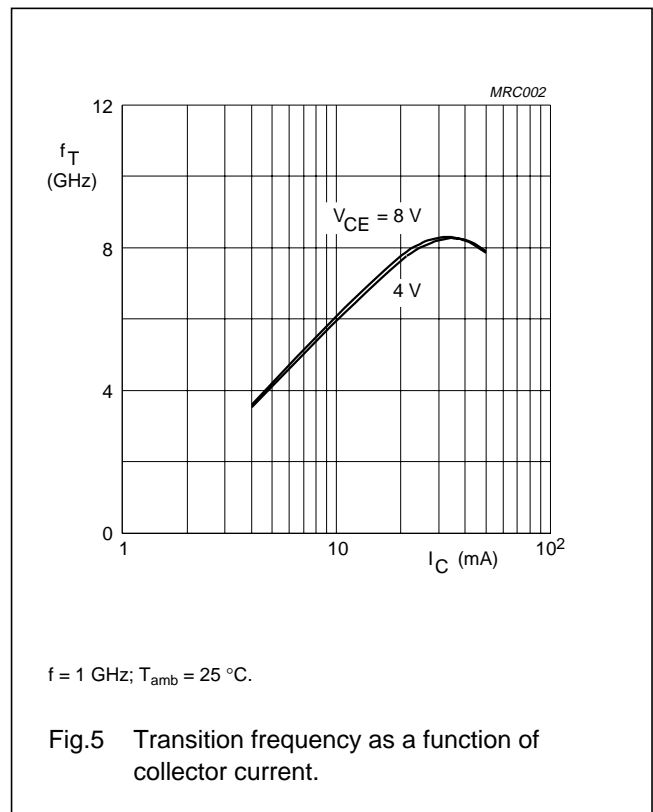
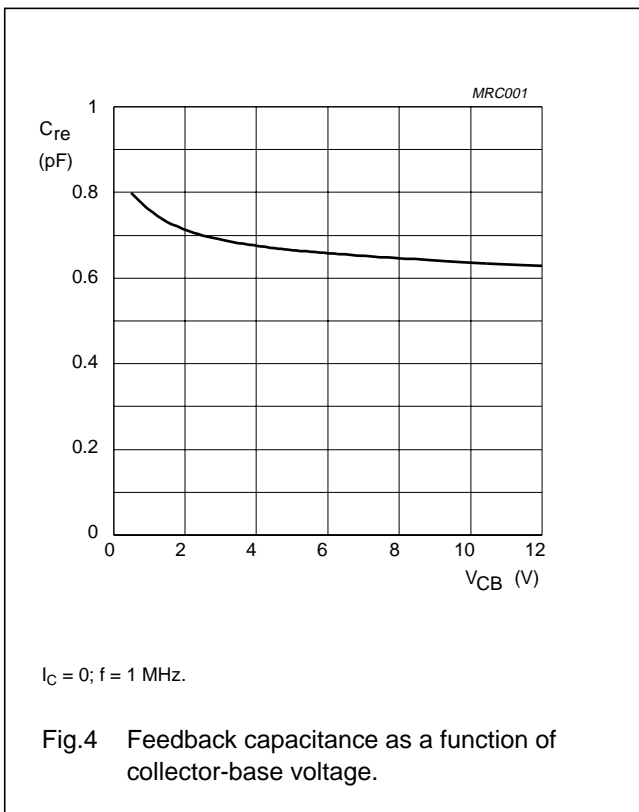
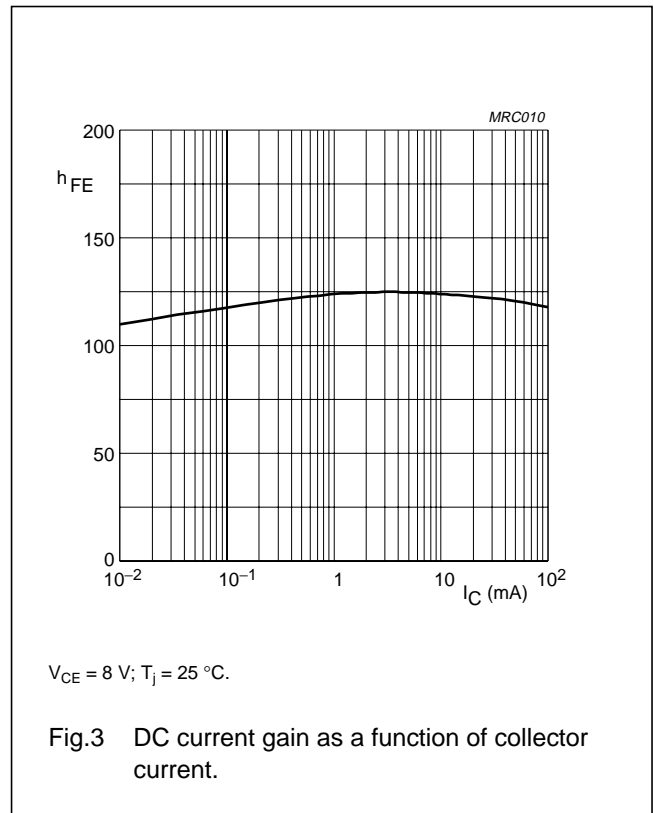
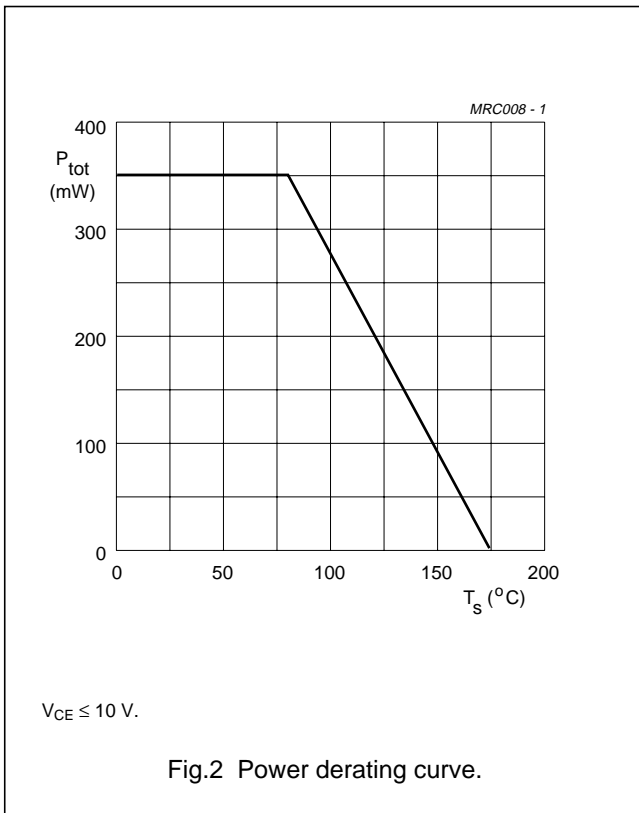
- G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero and

$$G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)} \text{ dB.}$$

- $I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $R_L = 50\text{ }\Omega$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$;
 $f_p = 900\text{ MHz}$; $f_q = 902\text{ MHz}$; measured at $f_{(2p-q)} = 898\text{ MHz}$ and at $f_{(2q-p)} = 904\text{ MHz}$.

NPN 9 GHz wideband transistor

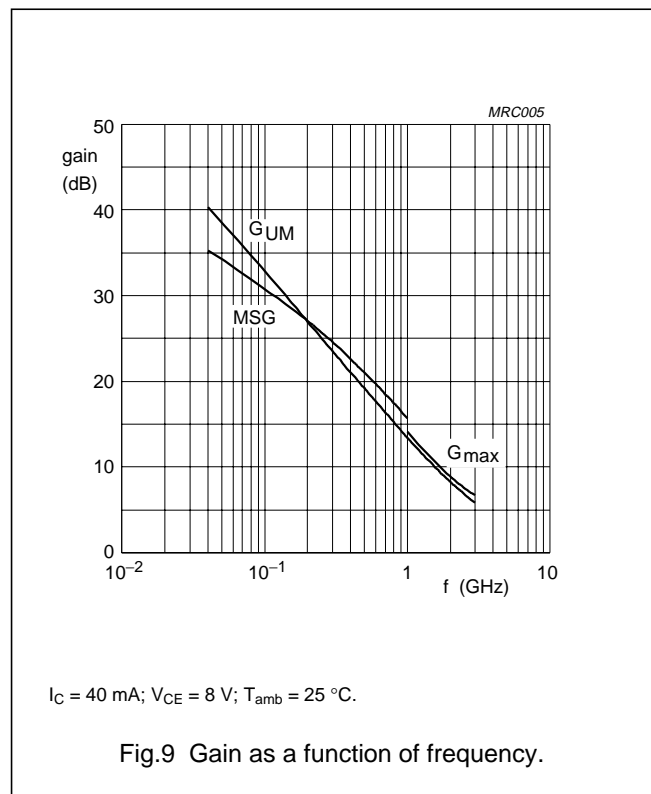
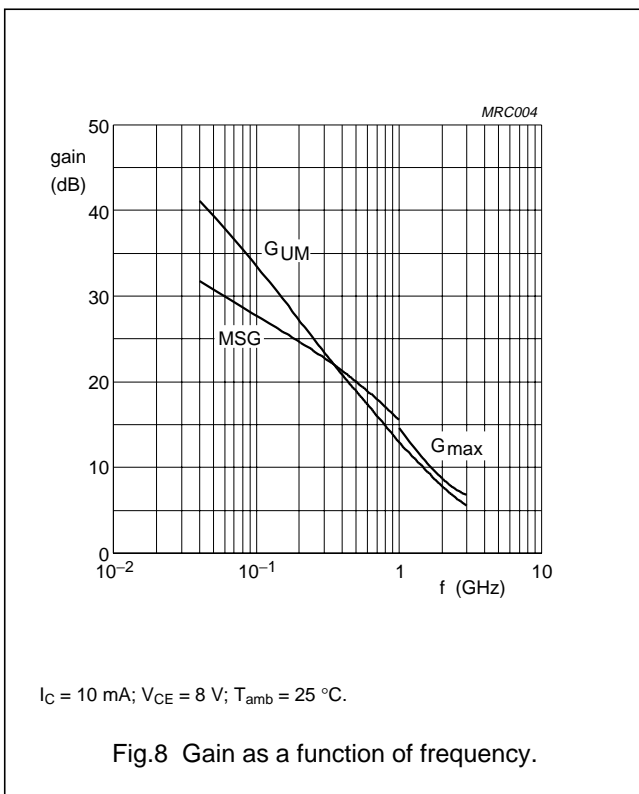
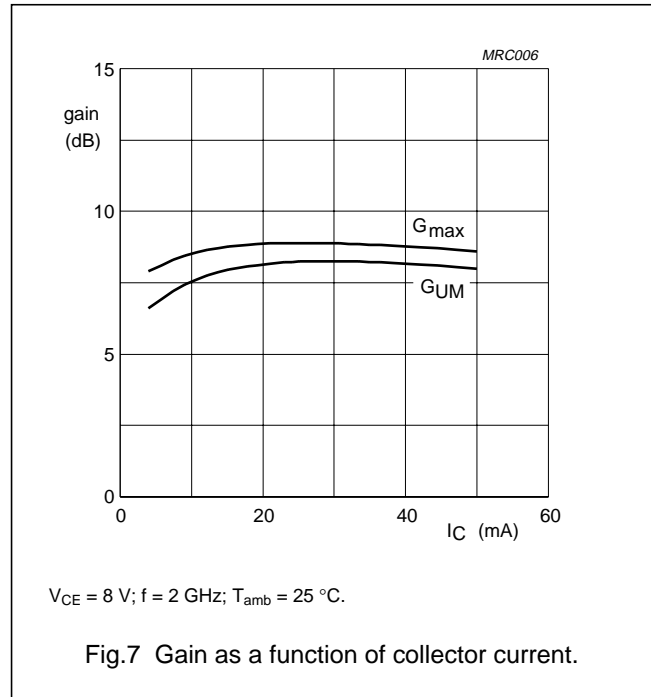
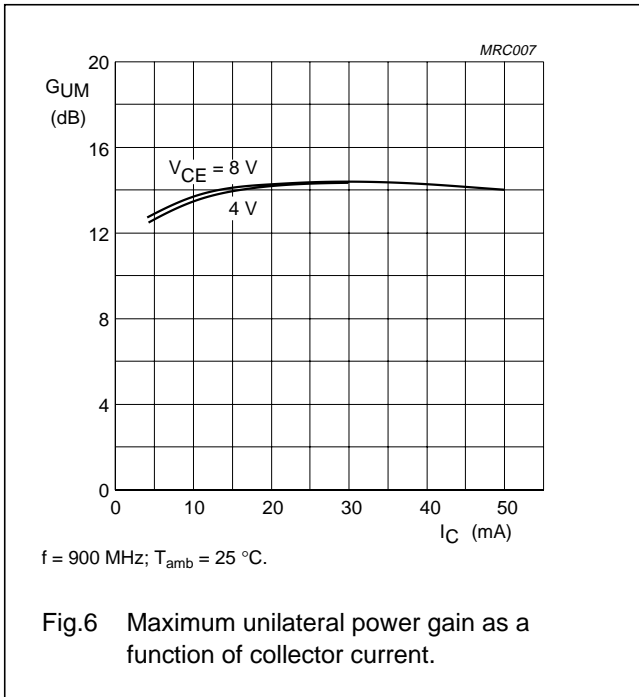
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NPN 9 GHz wideband transistor

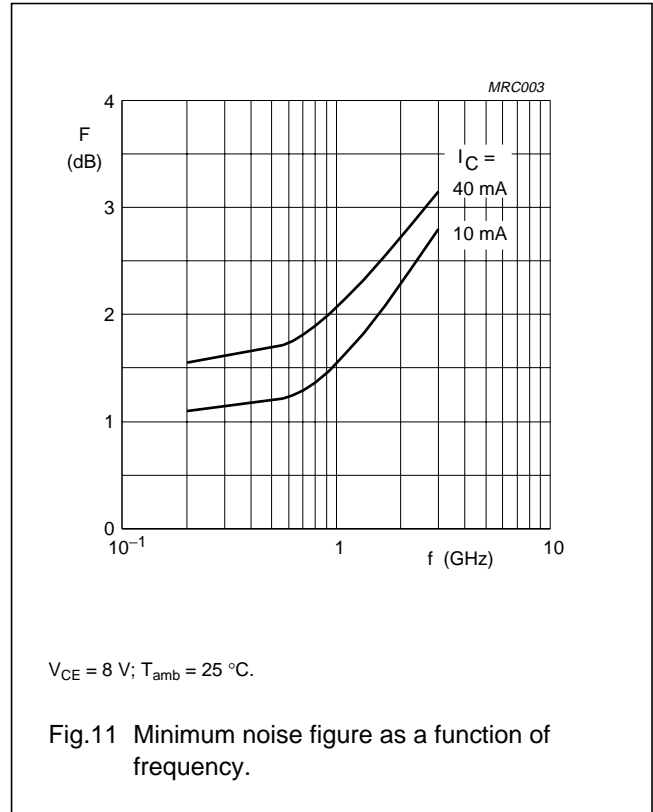
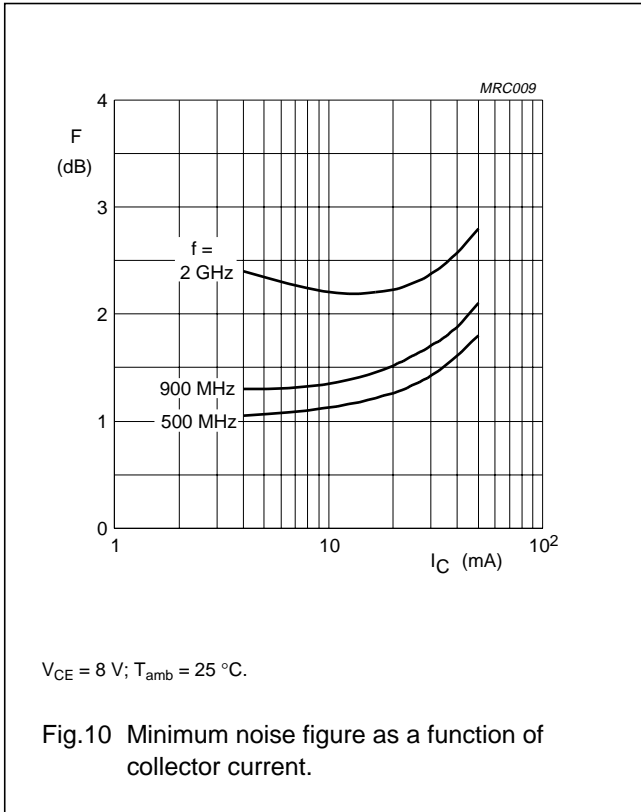
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In Figs 6 to 9, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain; G_{max} = maximum available gain.



NPN 9 GHz wideband transistor

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NPN 9 GHz wideband transistor

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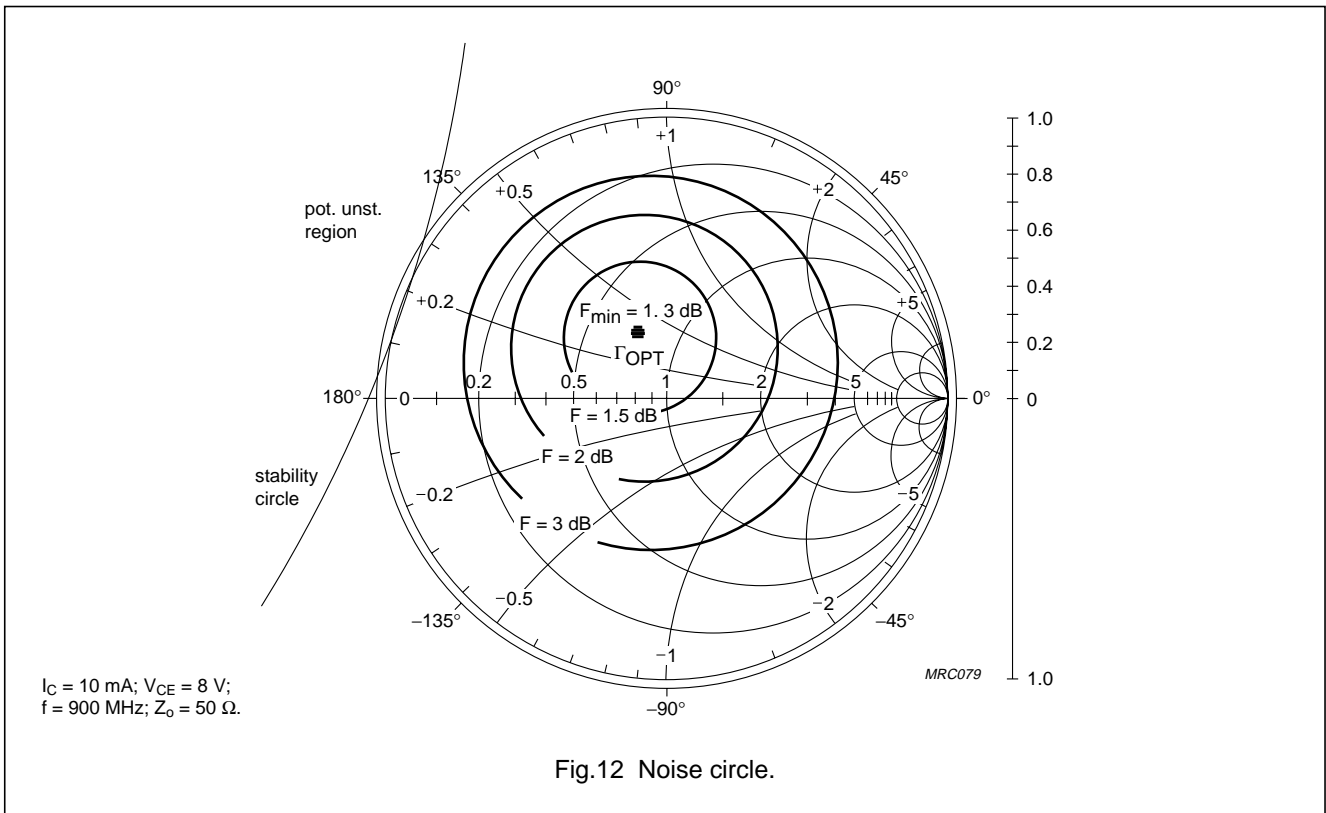


Fig.12 Noise circle.

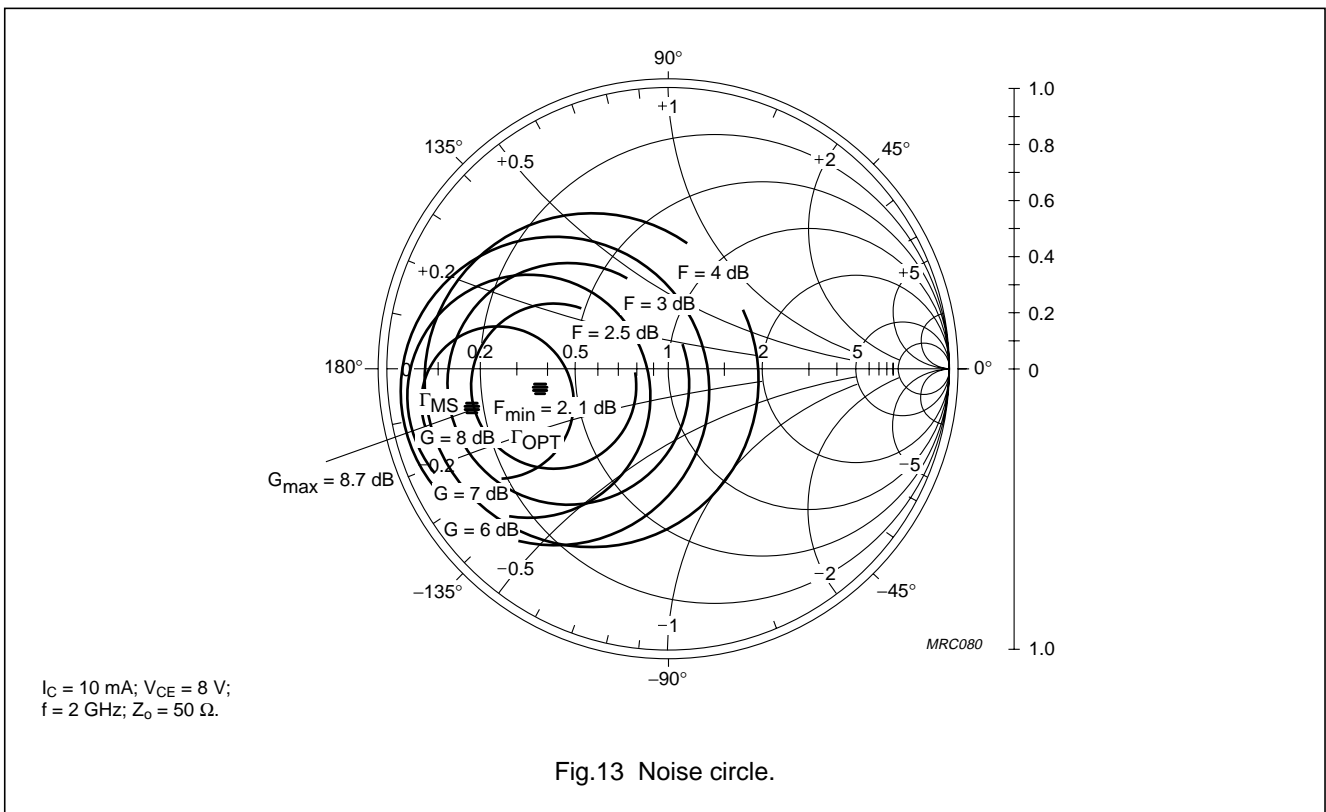
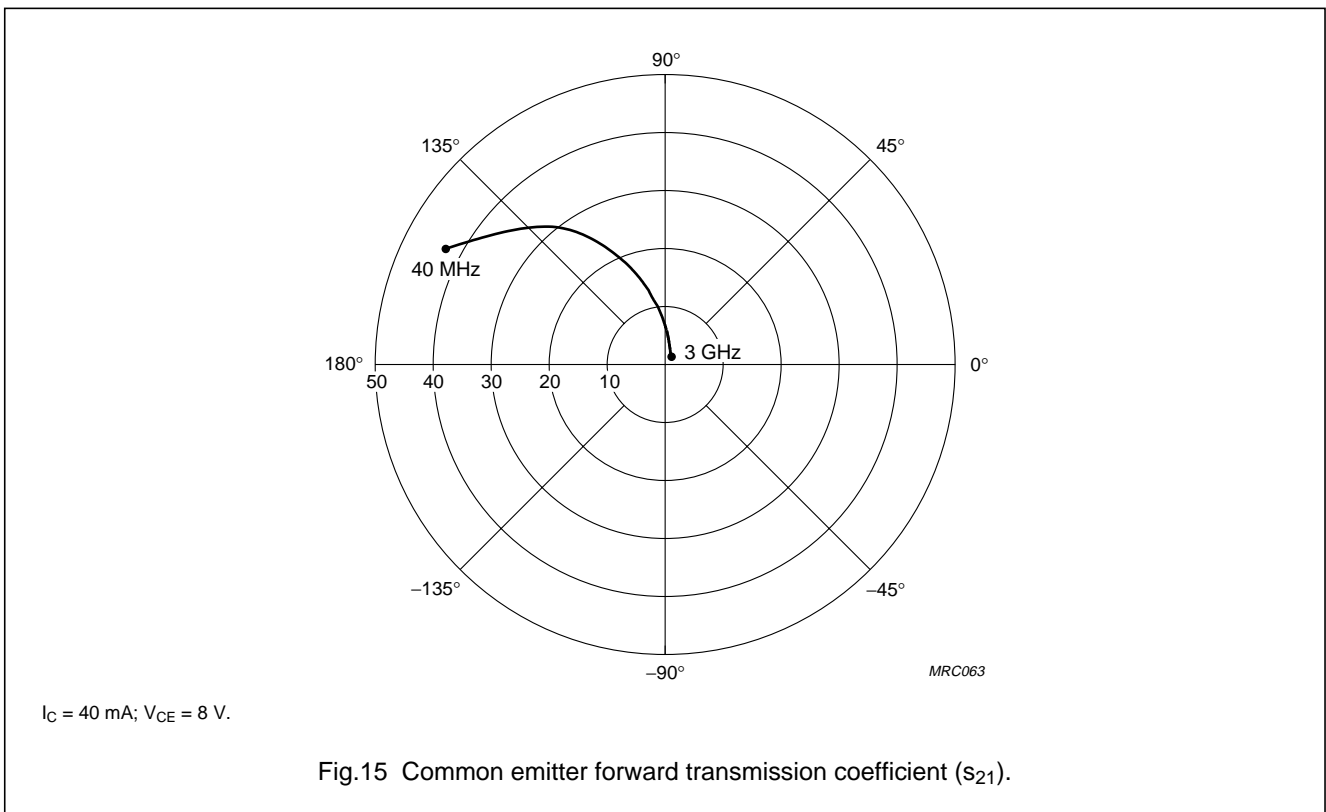
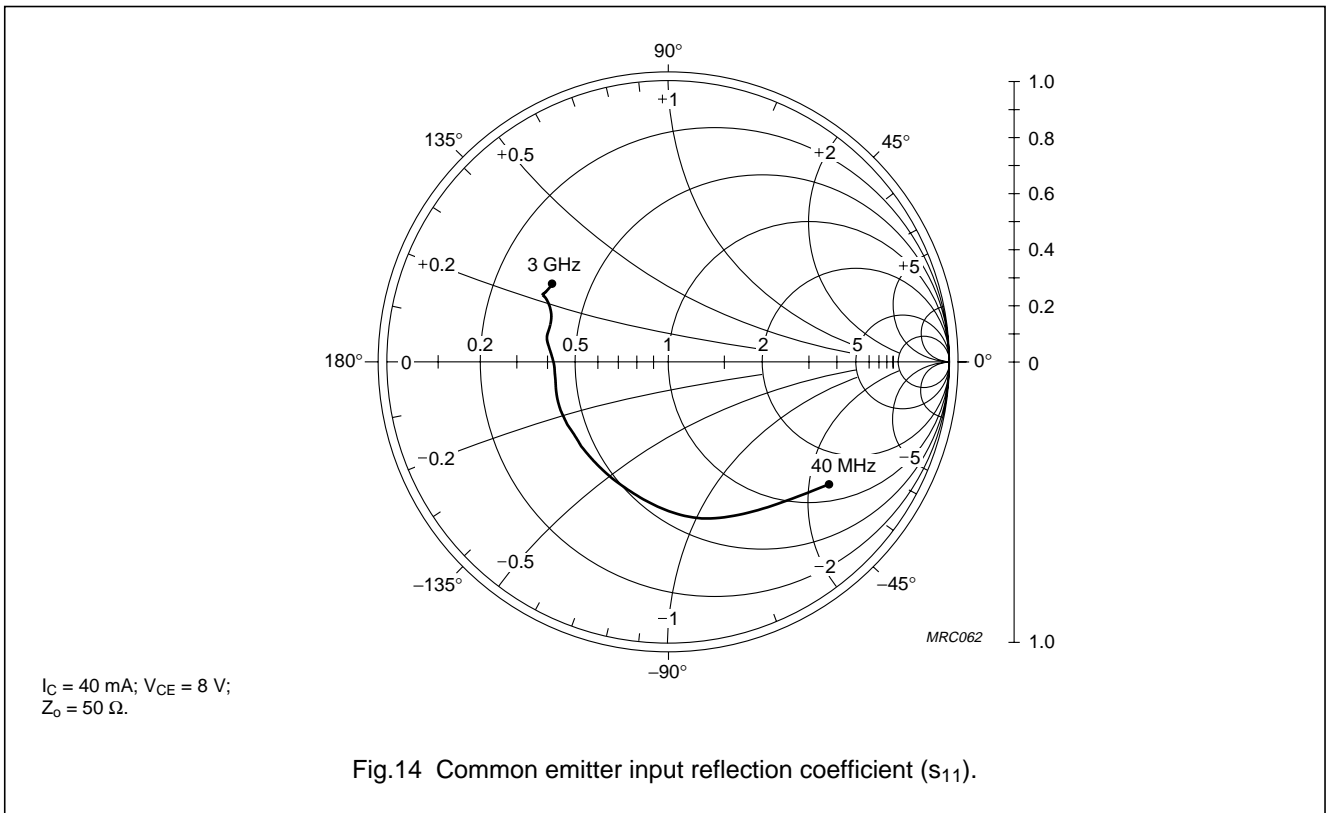


Fig.13 Noise circle.

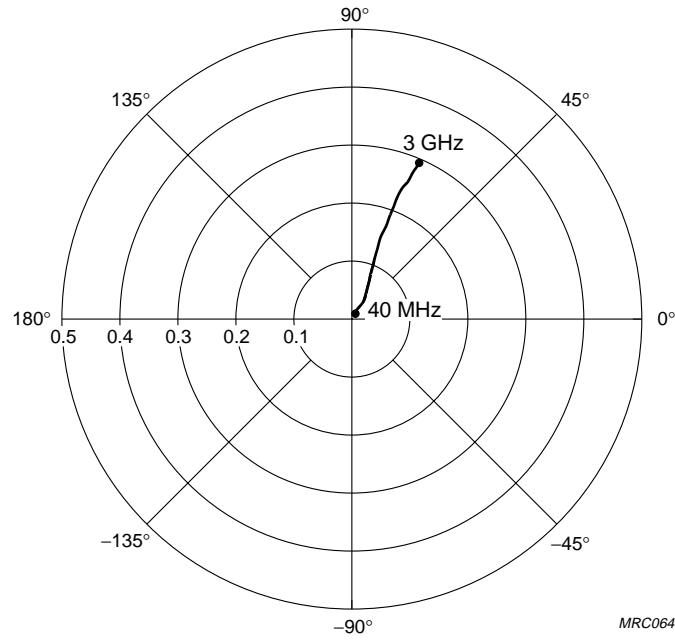
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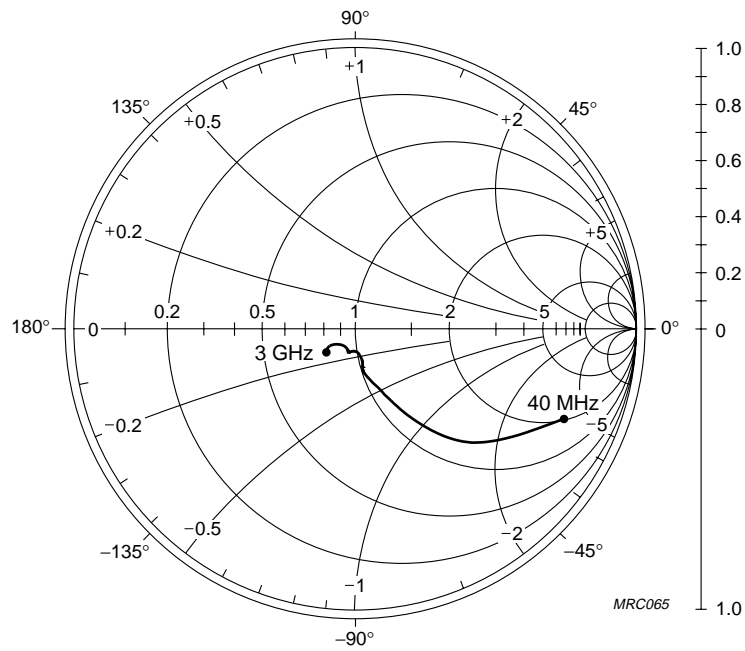
NPN 9 GHz wideband transistor

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$I_C = 40 \text{ mA}; V_{CE} = 8 \text{ V}.$

Fig.16 Common emitter reverse transmission coefficient (s_{12}).



$I_C = 40 \text{ mA}; V_{CE} = 8 \text{ V};$
 $Z_o = 50 \Omega.$

Fig.17 Common emitter output reflection coefficient (s_{22}).

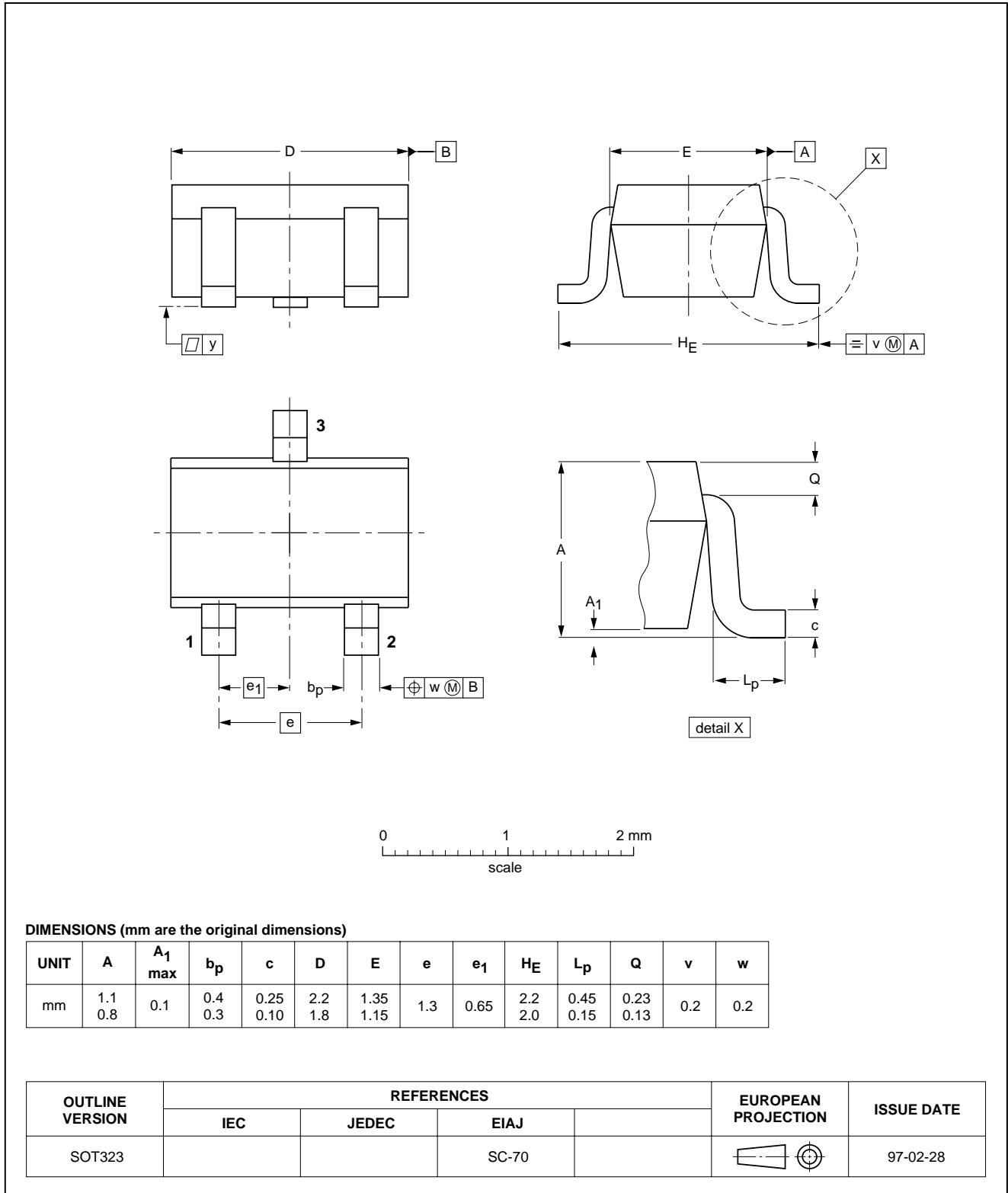
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



NPN 9 GHz wideband transistor

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
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Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
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Note

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Printed in The Netherlands

613516/04/pp12

Date of release: 2000 May 30

Document order number: 9397 750 07065

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